

Drafts

- BRS:
- BRS:
- BRS:
- BRS: knail
- BRS: 19 21 23
- BRS: 32with 33

Pending

Active

Failed

Saved

- S1: (1) 09948877
- S2: (1736) "KONINKLIKE PHILIPS" as.
- S3: (0) 10753914
- S4: (4) "20030109093" "6.670,671" pn.
- S5: (1) 10716703
- S6: (302806) (sonos monos)
- S7: (317007) (sonos monos mnos)
- S8: (9493) (charge near3 (strap\$4 trap\$4 ntride))
- S9: (116408) "g. bsum.
- S10: (103597) bi bitline bit adj line readline read adj line sense adj line
- S11: (90600) (wordline "WL" ( word digit control adj gate) adj line) (wo
- S12: (40497) (bi bitline bit adj line readline read adj line sense adj line)

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((bird adj beak  
) and ((sonos monos mnos)

)) and ((charge near3 (strap\$4 trap\$4 ntride))

)

Feb. 2005

U	Inventor	Document/Issue P	Title	Current	Current X	Retrieve	S	C	P	S	S	Image	Do P
1	Ramsey, US	654181/2003	2 Planar structure for non-volatile memo	257/32	257/E21.6								US 65418
2	Yoshino, A	US 200401/2004	2 Nonvolatile semiconductor memory de	257/31									US 20040
3	Lee, Chang	US 200500/2005	2 Nonvolatile memory devices and meth	438/25	438/265								US 20050
4	Moriya, Hir	US 200500/2005	2 NON-VOLATILE SEMICONDUCTOR M	438/26									US 20050
5	Lee, Chang	US 200301/2003	2 Nonvolatile memory devices and meth	365/20	257/E21.6								US 20030
6	Tenli, Satou	US 200300/2003	4 Non-volatile semiconductor memory a	257/31	257/E21.6								US 20030
7	Moriya, Hir	US 200300/2003	2 Nonvolatile semiconductor storage de	365/20	257/E21.6								US 20030
8	Lee, Chang	US 200300/2003	1 Method of forming non-volatile mem	438/25									US 20030
9	Goda, Aki	US 200300/2003	9 Semiconductor device and method of	257/49	257/E21.5								US 20030
10	Ramsey, US	200201/2002	2 Simultaneous formation of charge str	438/25	257/E21.6								US 20020

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